

CMOSプロセス(ファウンドリー)で作製されたマイクロ圧力センサ

by H.H. Wang et al.

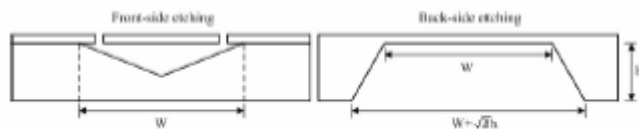


Fig. 1: Releasing the diaphragm via the front-side (left) and the back-side (right) etching methods by using KOH.

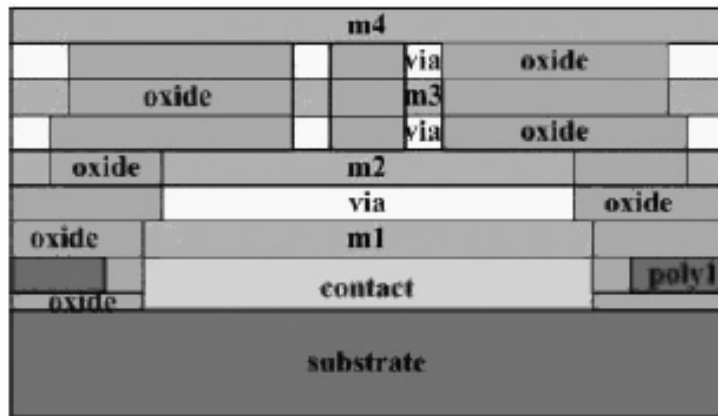


Fig. 3: The cross-section of a seashell-like pressure sensor depicting the layers stacked by the CMOS 2p4m process.

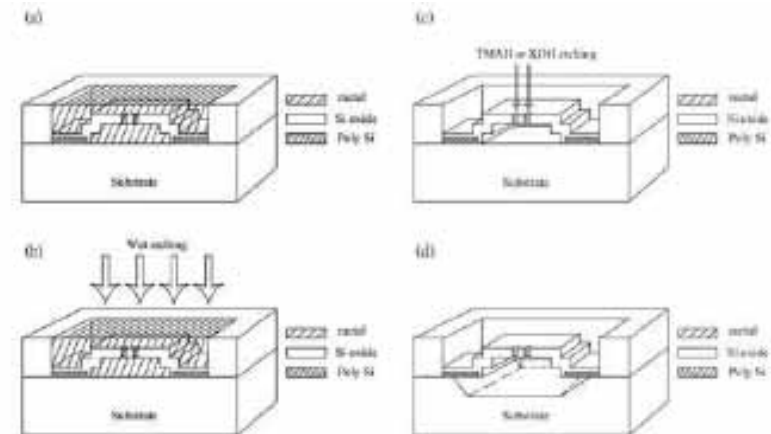


Fig. 6: Post process flow: (a-b) Using the etchants of Table 1 alternatively to remove the composite metal layers; (c-d) Using KOH to etch silicon substrate from front-side and release the poly-Si piezoresistors.

ポストプロセス

0.35 μm ルールの CMOS プロセスを利用
センササイズ: 50 μm \times 50 μm